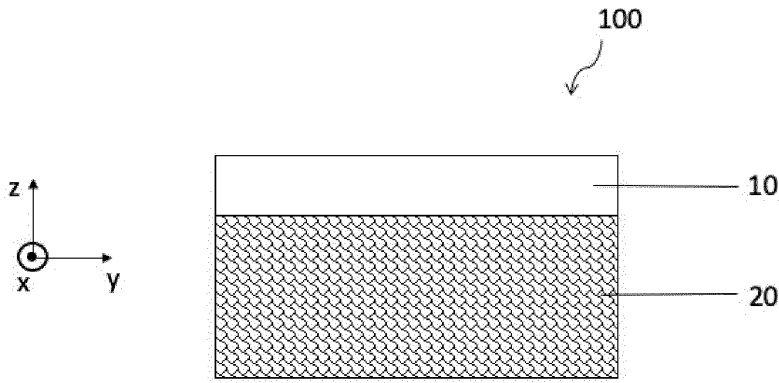


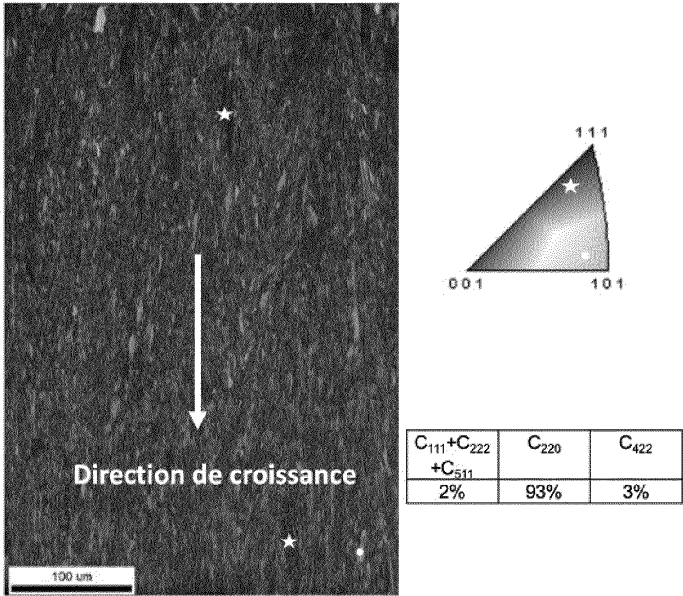
[Fig. 1]



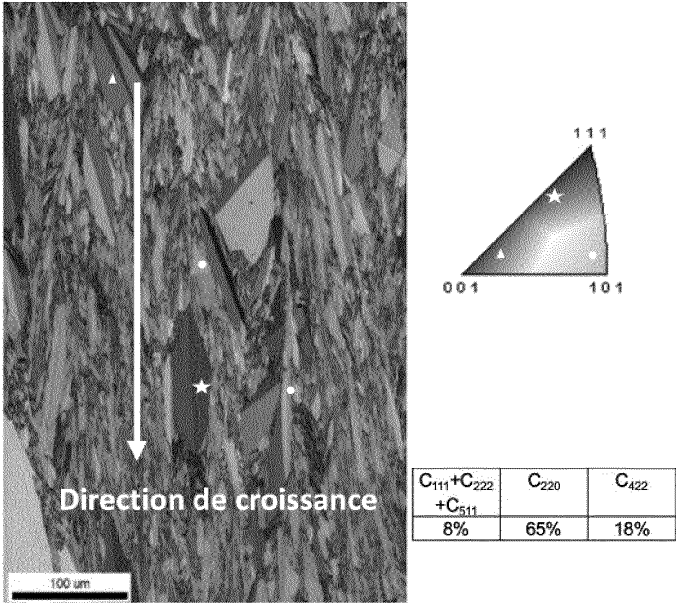
[Fig. 2]

hkl	Position 2 θ des pics [°]	Intensité I ₀ [%] théorique (Source ICDD)
111	[34,940 ° - 36,345 °]	100
200	[41,230 ° - 41,584 °]	23
220	[59,494 ° - 60,452 °]	57
311	[71,167 ° - 72,348 °]	48
222	[75,303 ° - 75,749 °]	10
400	[89,575 ° - 90,298 °]	12
331	[100,250 ° - 101,537 °]	25
420	[104,045 ° - 104,885 °]	13
422	[119,276 ° - 120,418 °]	14
511	[132,367 ° - 134,021 °]	15

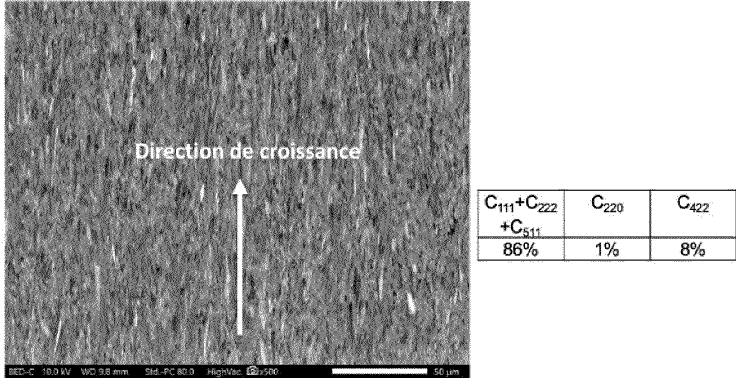
[Fig. 3a]



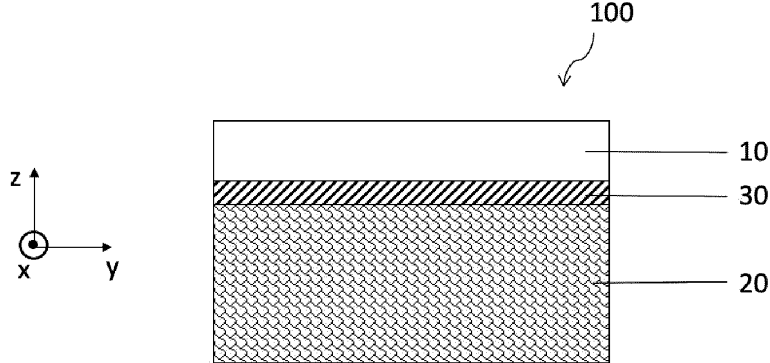
[Fig. 3b]



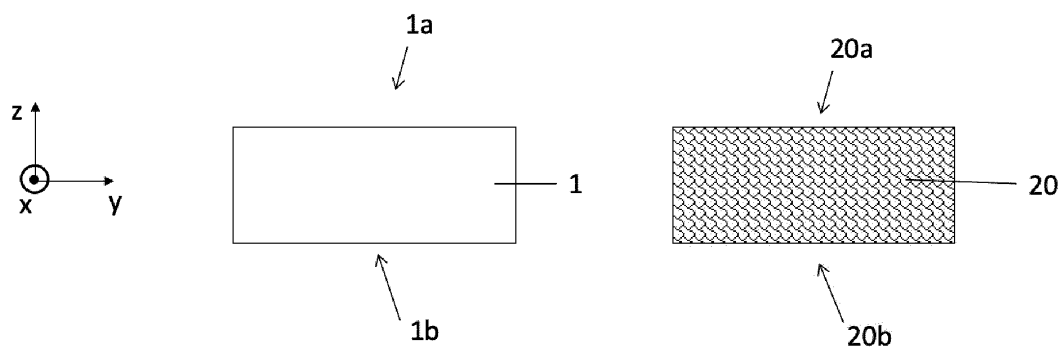
[Fig. 3c]



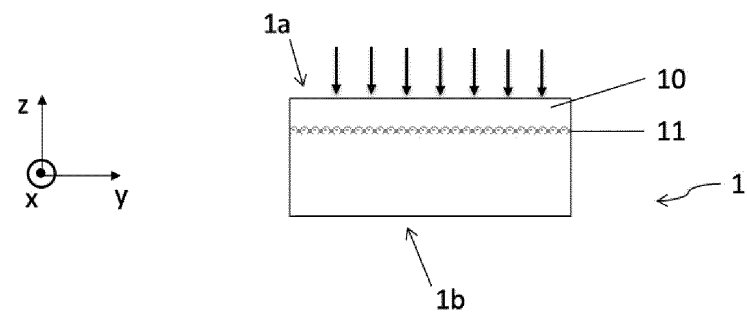
[Fig. 4]



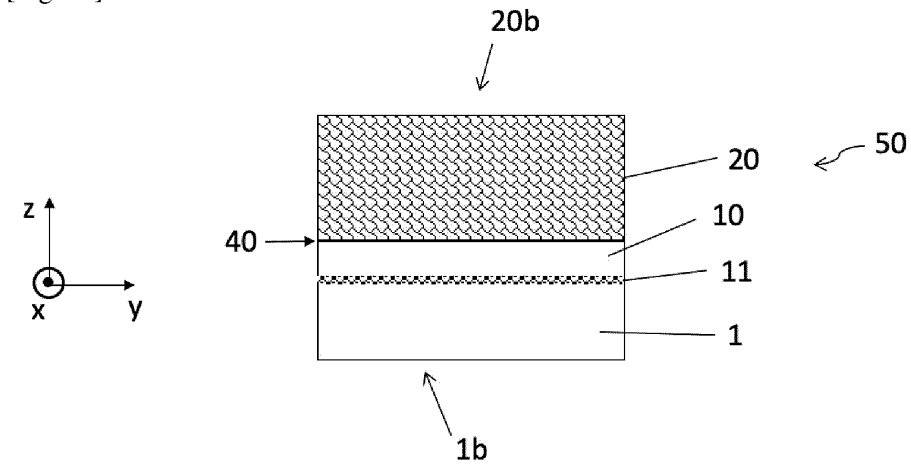
[Fig. 5a]



[Fig. 5b]

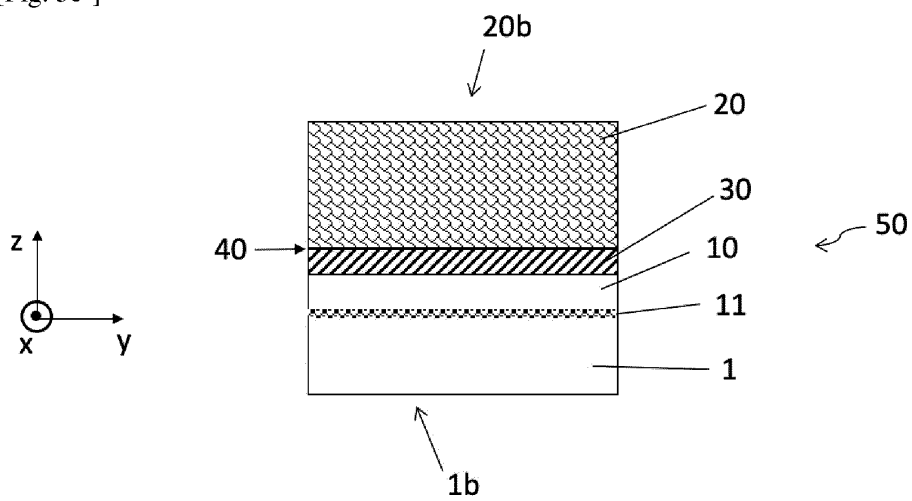


[Fig. 5c]

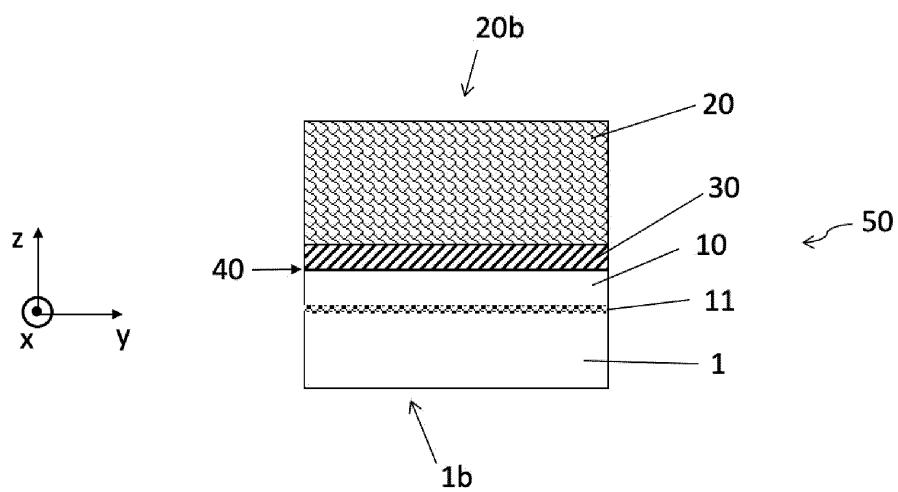


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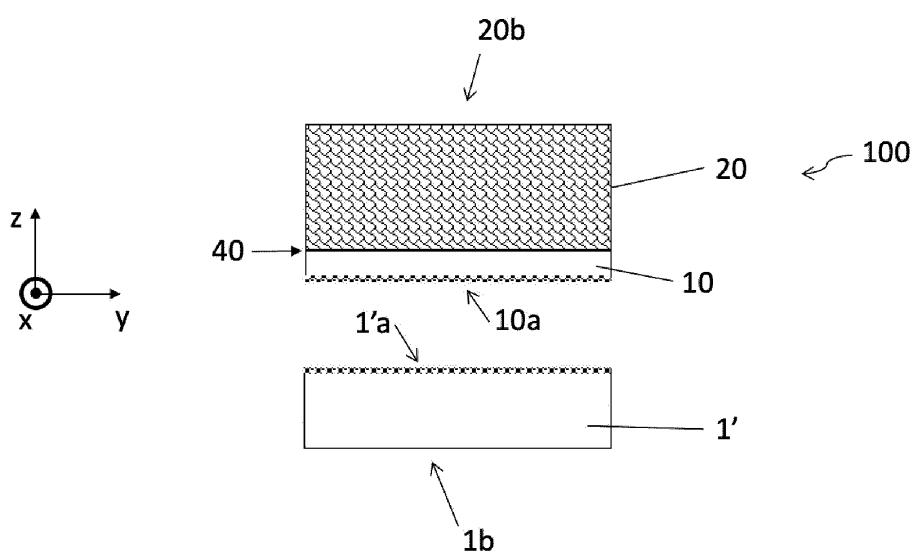
[Fig. 5c']



[Fig. 5c'']



[Fig. 5d]



[Fig. 6]

#	1	2	3	4	5
Température (°C)	1277	1277	1277	1327	1327
Gaz précurseur MTCS (mbar)	23	8	16	16	16
Gaz dopant NH3 (%)	3	6	4	4	6
% C ₂₂₀	1	1	93	65	7
% C ₁₁₁ + C ₂₂₂ +C ₅₁₁	9	86	2	8	20
% C ₄₂₂	80	8	3	18	54
Dopant N (at/cm ³)	8 x10 ¹⁹	7 x10 ²⁰	1,8 x10 ²⁰	2,2x10 ²⁰	6,8x10 ²⁰
Résistivité (mOhm.cm)	16	1,1	5	3,3	0,9
Conductibilité thermique (W/m/K)	210	52	270	215	130
Epaisseur Disque p-SiC brut (um)	650	650	650	800	800
Courbure Disque brut p-SiC (150mm) [um]	850	190	210	235	650
Courbure Substrat Support 20 en p-SiC (150mm) [um]	-	< 100	< 100	< 100	-